

**IN THE SPECIFICATION:**

Please amend paragraph [0029] as follows:

Therefore, as described above, this aspect of the invention provides a chlorine-based etch process for TiN in trenches, which provides high selectivity to both silicon (including n-doped polysilicon) and dielectric mask materials (e.g. silicon nitride, silicon dioxide). The etch process uses low DC bias to provide selectivity to the mask material. Typical operating ranges are 1- 50 mT pressure, 50-5000 W decoupled source power, less than 100W bias power to the wafer. The reactive gas feedstocks contain less than 5% fluorine based halogens (e.g. ~~CF<sub>4</sub>~~, ~~SF<sub>6</sub>~~, ~~NF<sub>3</sub>~~, CF<sub>4</sub>, SF<sub>6</sub>, NF<sub>3</sub>, etc.), and the balance ~~Cl<sub>2</sub>~~ (~~Cl<sub>2</sub>~~, ~~BCl<sub>3</sub>~~, Cl<sub>2</sub>, BCl<sub>3</sub>, HCl) or Br (HBr, Br<sub>2</sub>, ~~Br<sub>2</sub>~~) based reactants. Diluent gases may additionally be added in any range from 0% to 90% of the total feed, and can include He, Ar, N<sub>2</sub>, Kr, etc.